

FORM PTO-1449  U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE  LIST OF REFERENCES CITED BY APPLICANT  (Use several sheets if necessary)	ATTY. DOCKET NO. <b>12007-0074</b>	SERIAL NO. <b>10/580,653</b>
	APPLICANT <b>Wolfgang STOLZ et al.</b>	
	FILING DATE <b>05/25/2006</b>	GROUP ART UNIT 2826 <b>Not yet assigned</b>

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NO.	DATE	NAME	CLASS	SUB- CLASS	FILING DATE
---------------------	-----------------	------	------	-------	---------------	----------------

## FOREIGN PATENT DOCUMENTS

DOCUMENT NO.	DATE	COUNTRY	CLASS	SUB- CLASS	TRANSLATION YES NO PART.
-----------------	------	---------	-------	---------------	-----------------------------

## OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)

/KQ/	1.	C. Ellmers, et al., "GaAs-based VCSEL-structures with strain-compensated (GaIn)As/Ga(PAs)-MQWH active regions grown by using TBAs and TBP", Journal of Crystal Growth 195 (1998) 630-636
	2.	C. Ellmers, et al., "Optically pumped (GaIn)As/Ga(PAs) vertical-cavity surface-emitting lasers with optimized dynamics", American Institute of Physics; Applied Physics Letters, Volume 74, No. 10, March 8, 1999, pgs. 1367-1369
	3.	Y. Okuno, et al., "1.3 $\mu$ m wavelength vertical cavity surface emitting laser fabricated by orientation-mismatched wafer bonding: A prospect for polarization control", American Institute of Physics; Applied Physics Letters, Volume 82, No. 15, April 14, 2003, pgs. 2377-2379
	4.	S. Ae, et al., "Low threshold $\lambda = 1.3 \mu$ m multi-quantum well laser diodes grown by metalorganic vapor phase epitaxy using tertiarybutylarsine and tertiarybutylphosphine precursors", Journal of Crystal Growth 145 (1994) 852-857
	5.	I. Kim, et al., "Composition control of InGaAsP in metalorganic chemical vapor deposition using tertiarybutylphosphine and tertiarybutylarsine <sup>1</sup> ", Journal of Crystal Growth 193 (1998) 293-299
↓	6.	A. Ougazzaden, et al., "High performance strained MQW lasers at 1.3 $\mu$ m by MOVPE using arsine generator system", ELECTRONIC LETTERS, Vol. 30, No. 20, September 29, 1994, pgs. 1681-1682
/KQ/	7.	H.Q. Hou, et al., "High-Performance 1.06- $\mu$ m Selectively Oxidized Vertical-Cavity Surface-Emitting Lasers with InGaAs-GaAsP Strain-Compensated Quantum Wells", IEEE Photonics Technology Letters, Vol. 9, No. 8, August 1997, pgs. 1057-1059

EXAMINER  /Kevin Quinto/	DATE CONSIDERED  01/02/2008
--------------------------------	-----------------------------------

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.